

Effect of strain on the dynamics of optically induced metal-insulator transitions of VO_2 thin films

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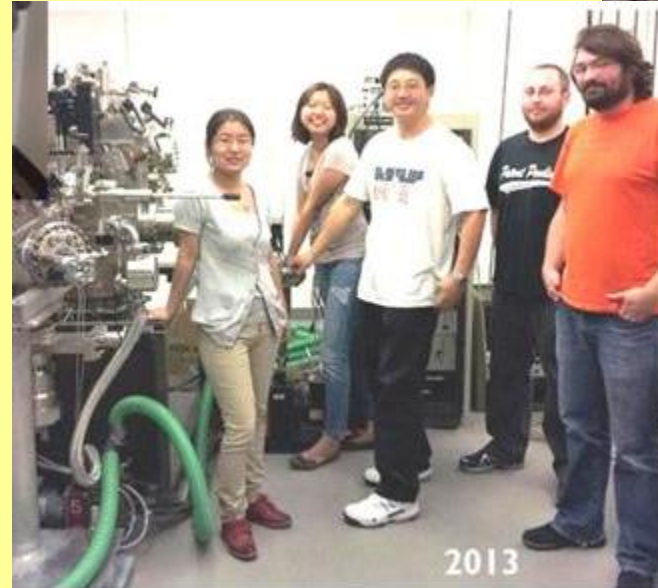
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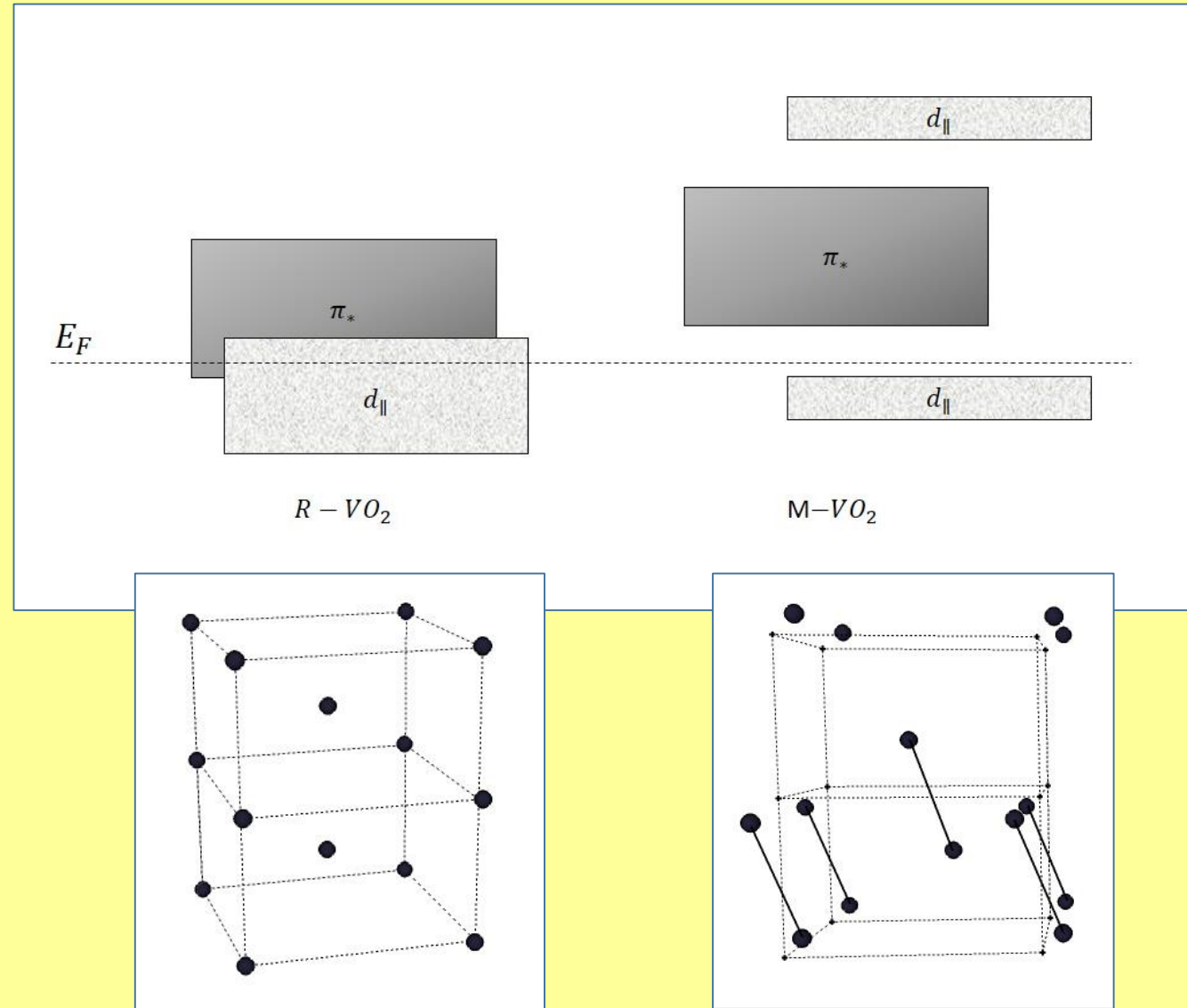
S. Kittiwatanakul



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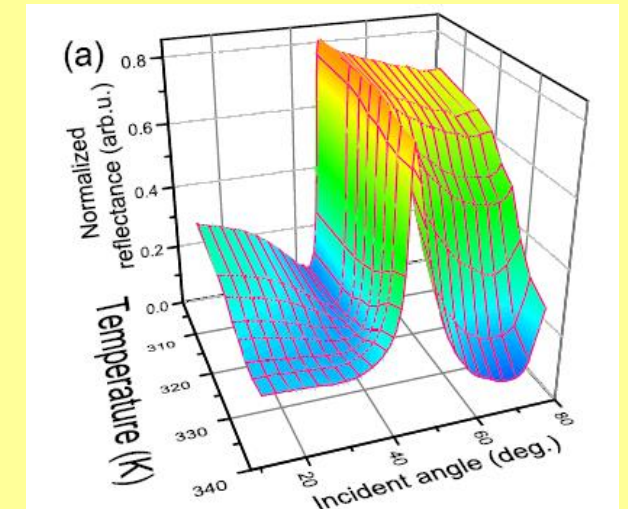
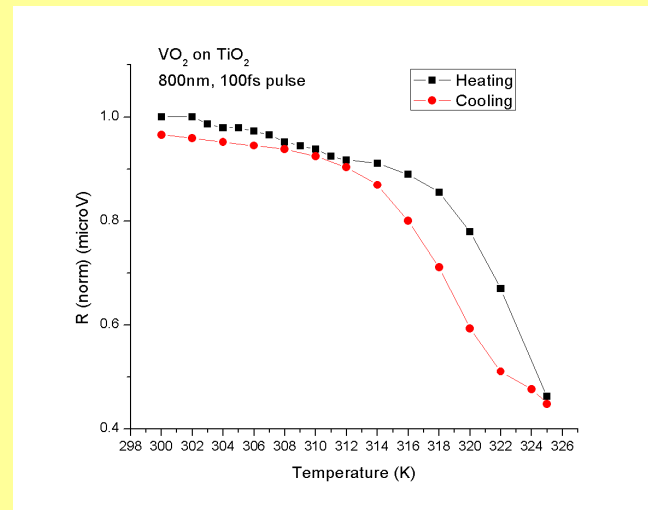
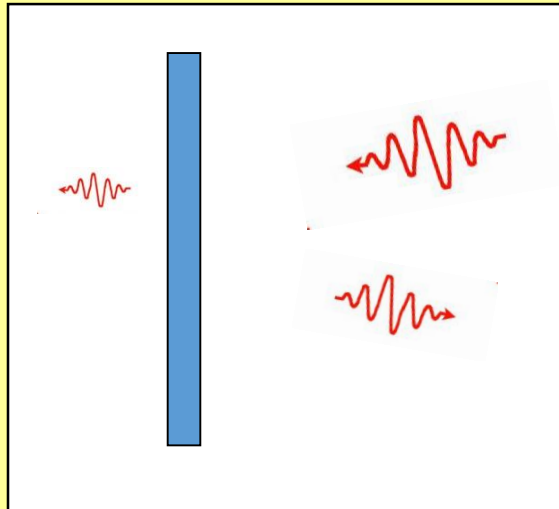
VO_2 Phase transition

- Highly correlated material
- Undergoes metal-insulator transition when heated (340K)
- Reversible in thin films



Exciting applications

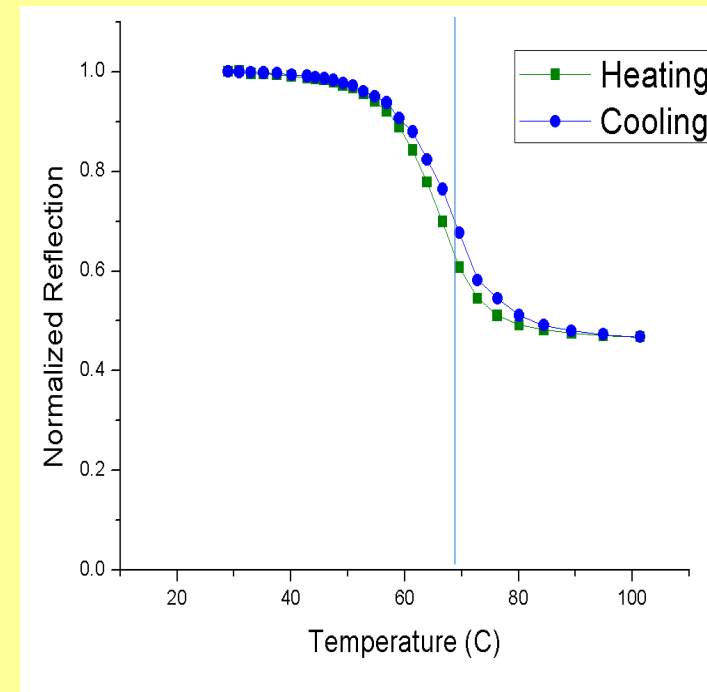
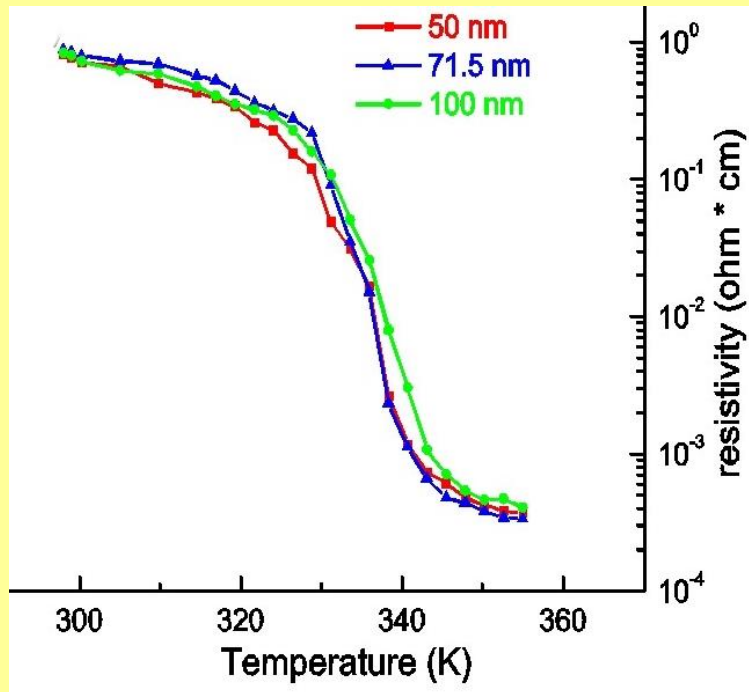
- Many possible novel technologies with VO_2



- The better we understand the mechanisms for the transition and how different substrates and microstructure affects them, the better we'll be able to tune the film for specific needs.

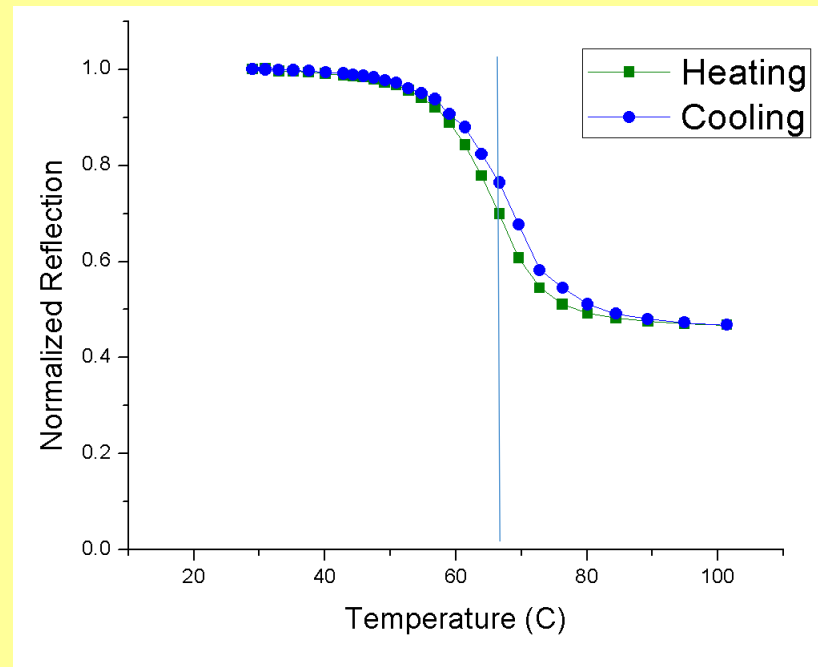
Probing the Metal-insulator transition (MIT)

- Large change in conductivity/index of refraction

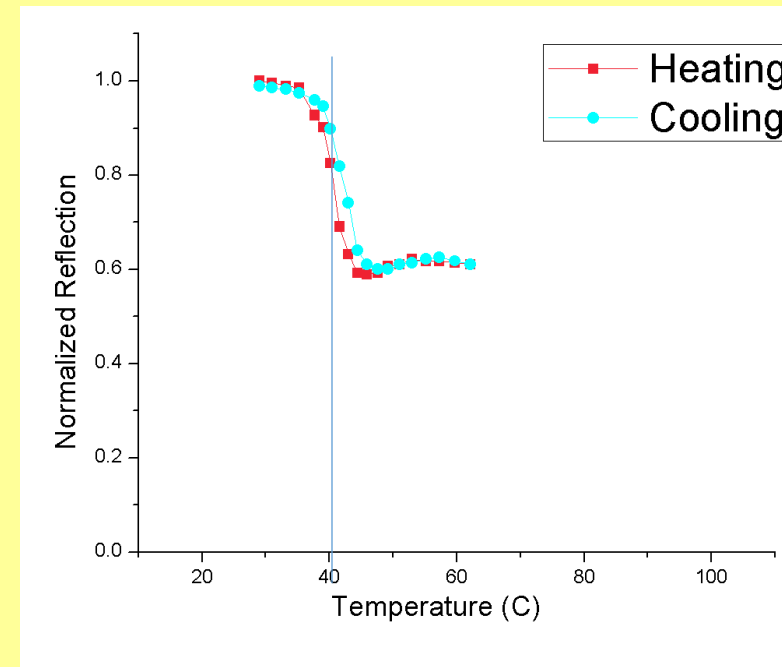


Effect on microstructure on Metal-Insulator Transition

VO_2 on Al_2O_3
 $T_c=341\text{K}$

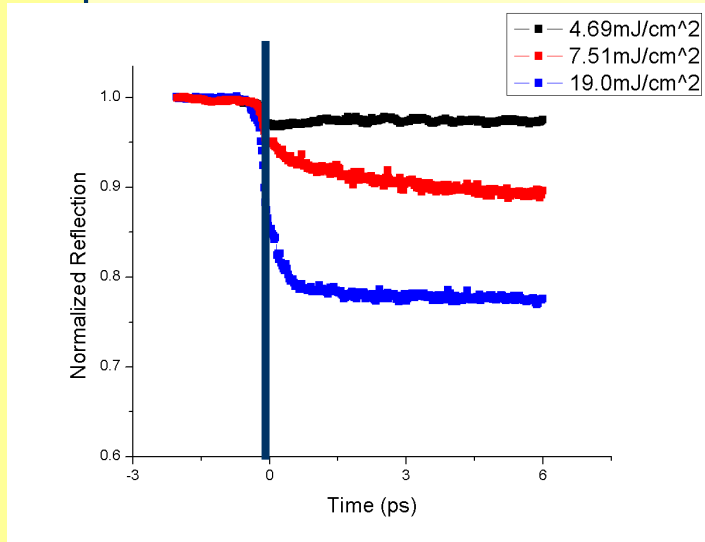
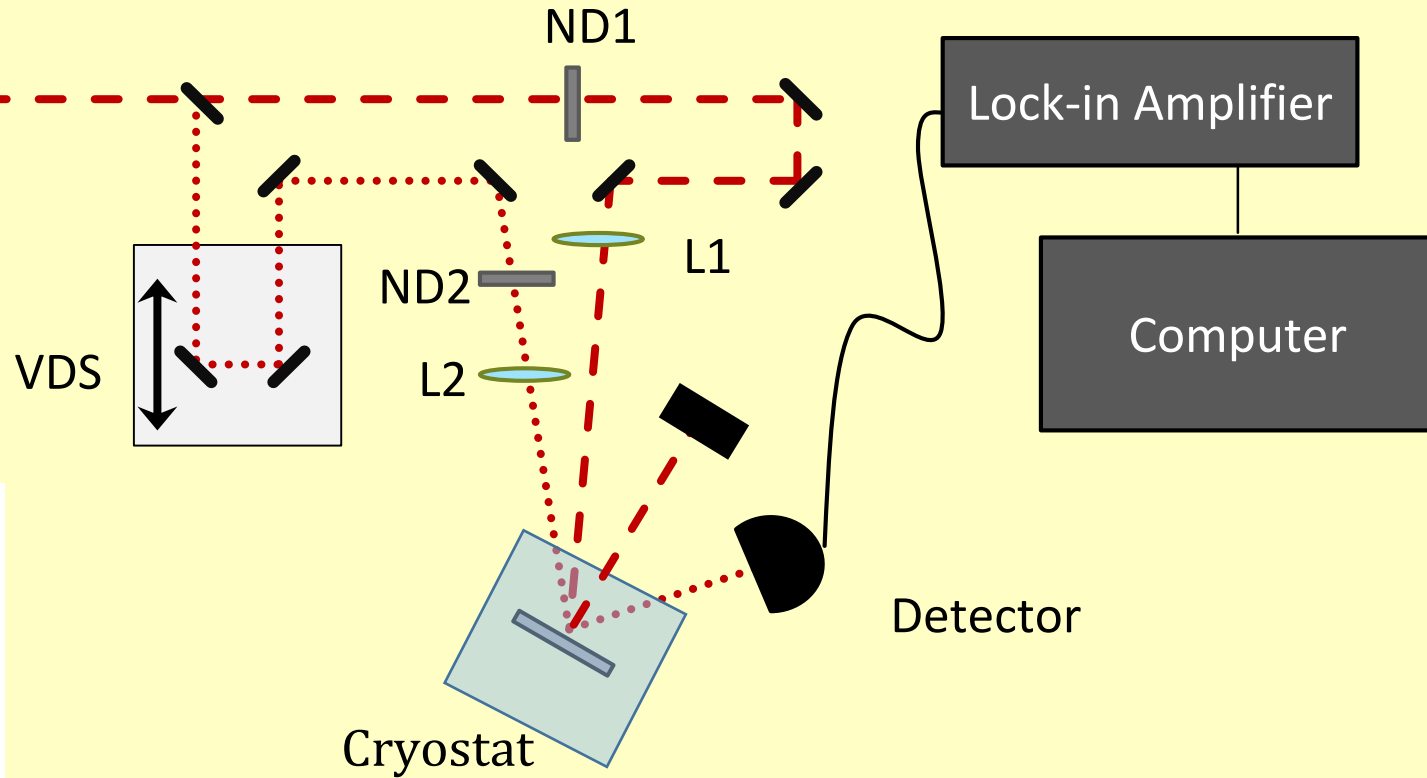


VO_2 on TiO_2
 $T_c=306\text{K}$



Experimental Set up for Pump Probe

Femtosecond pulses



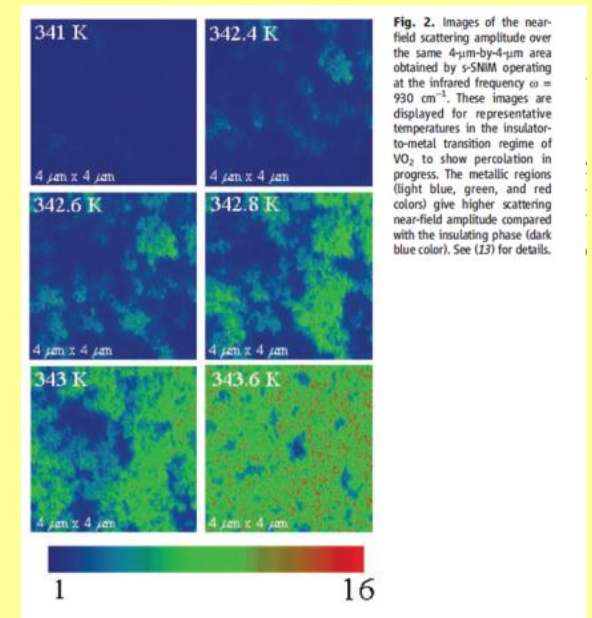
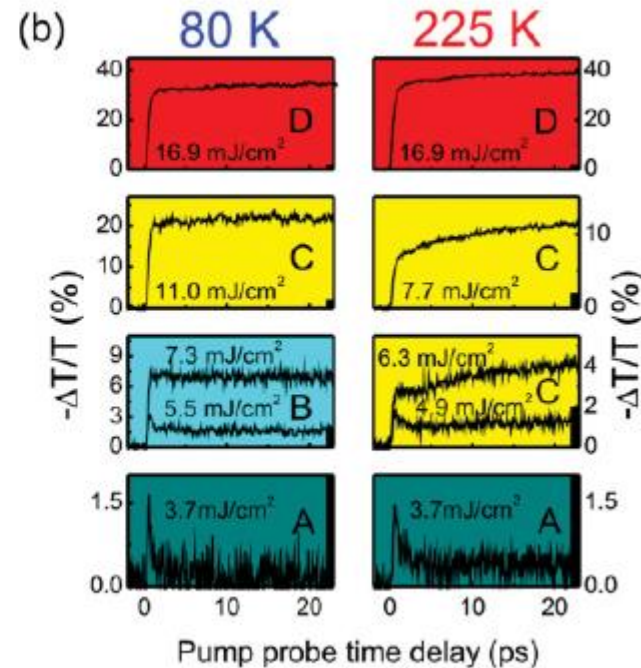
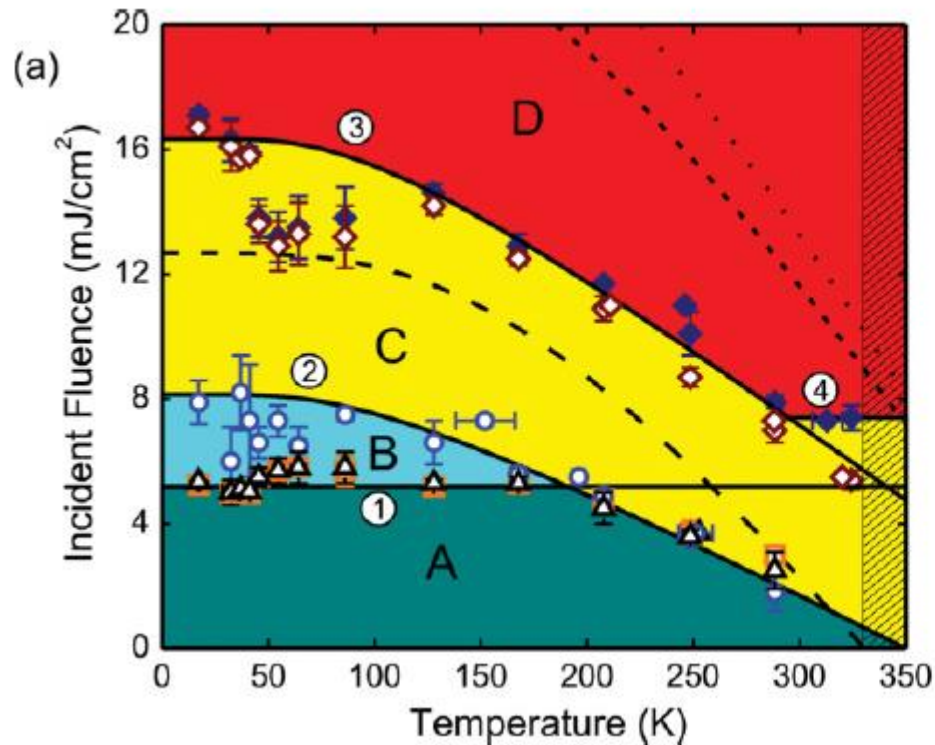
Phase diagram of the ultrafast photoinduced insulator-metal transition in vanadium dioxide

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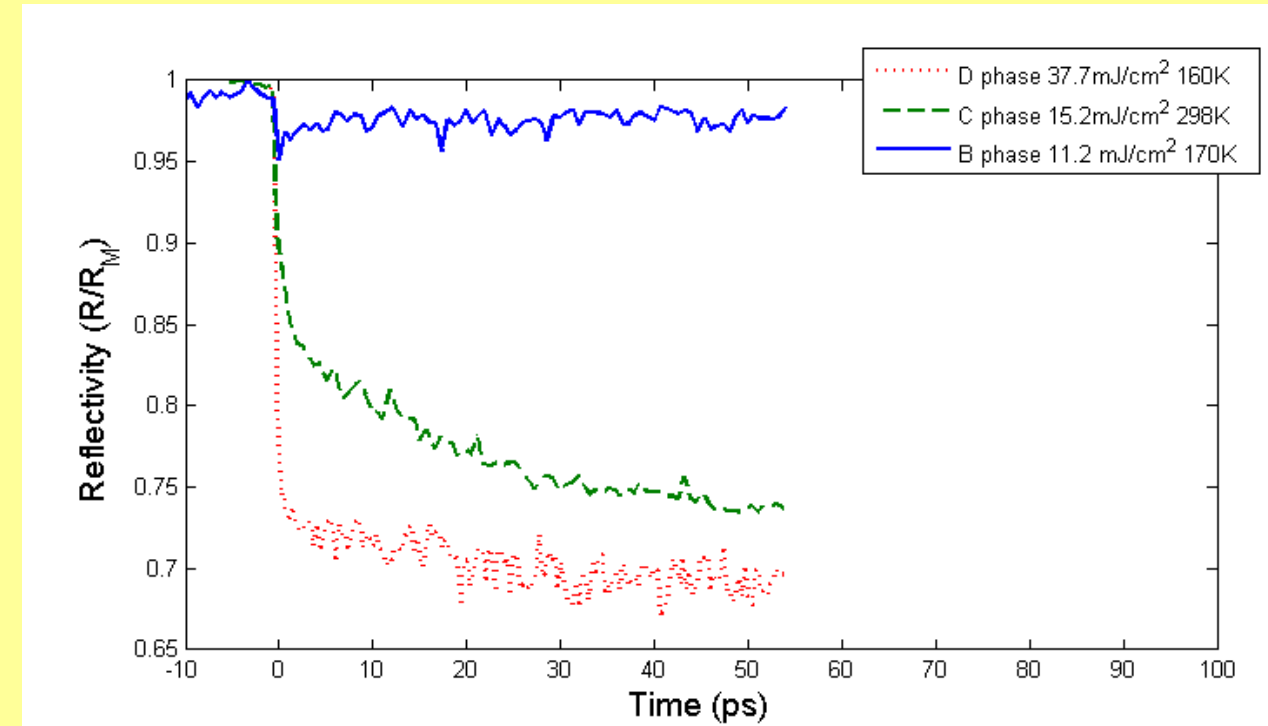
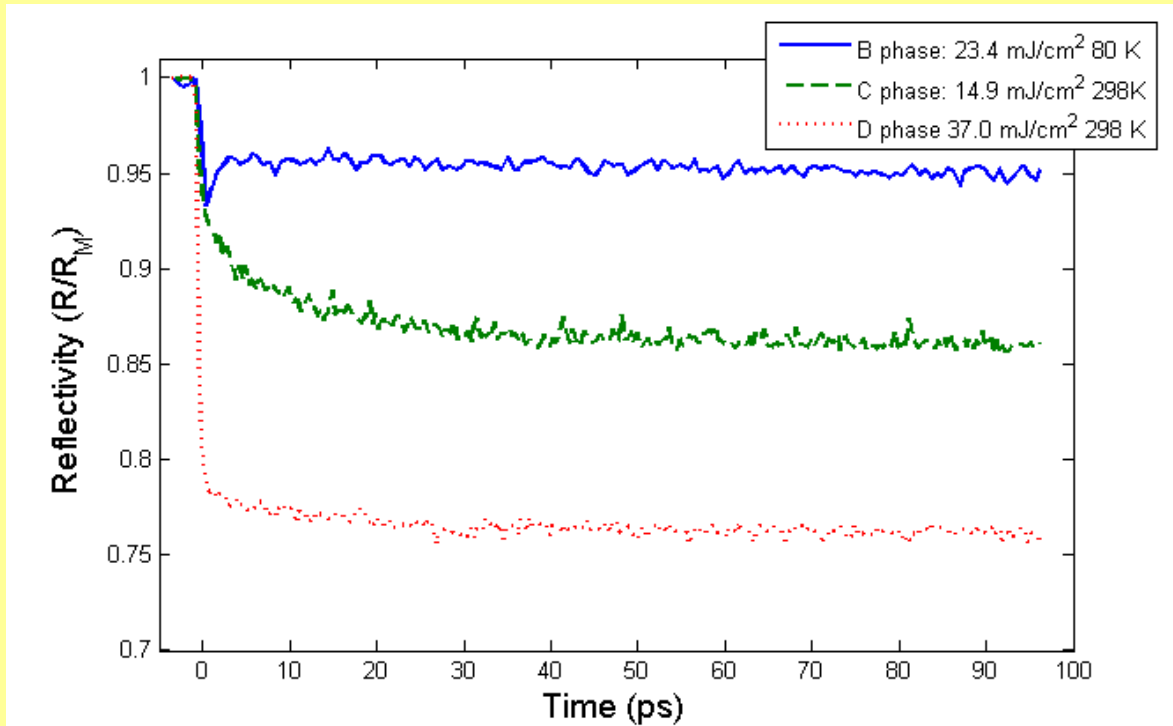
(Received 4 December 2011; published 11 April 2012)



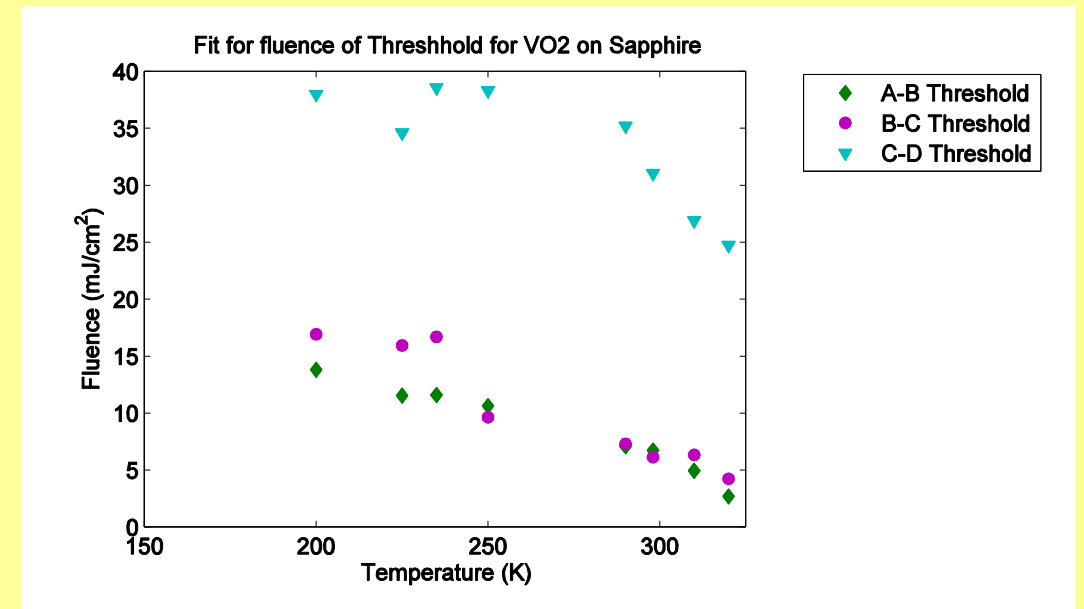
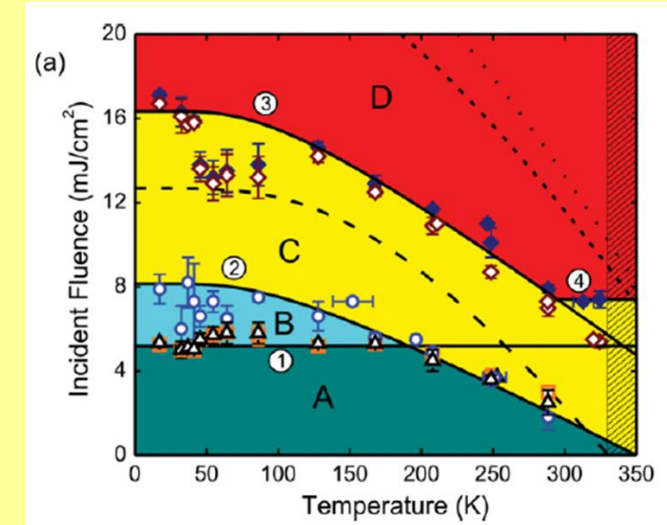
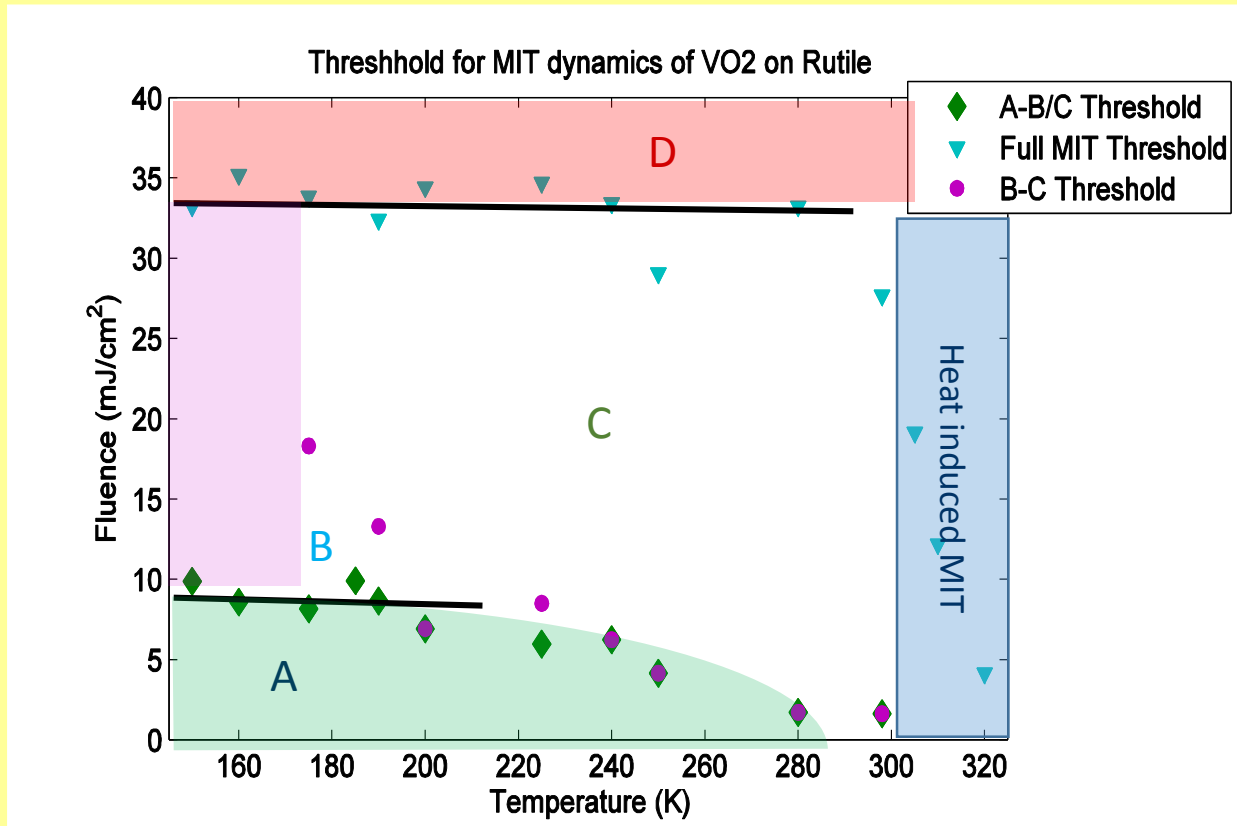
M.M. Qazilbash, M. Brehm, B.-G. Chae, P.-C. Ho, G.O. Andreev, B.-J. Kim, S.J. Yun, a V Balatsky, M.B. Maple, F. Keilmann, H.-T. Kim, and D.N. Basov, Science (New York, N.Y.) 318, 1750 (2007).

Comparing dynamics of MIT

- Pump probe measurements at 800nm



Phase Diagram for VO_2 Dynamics



Conclusion & Future Work

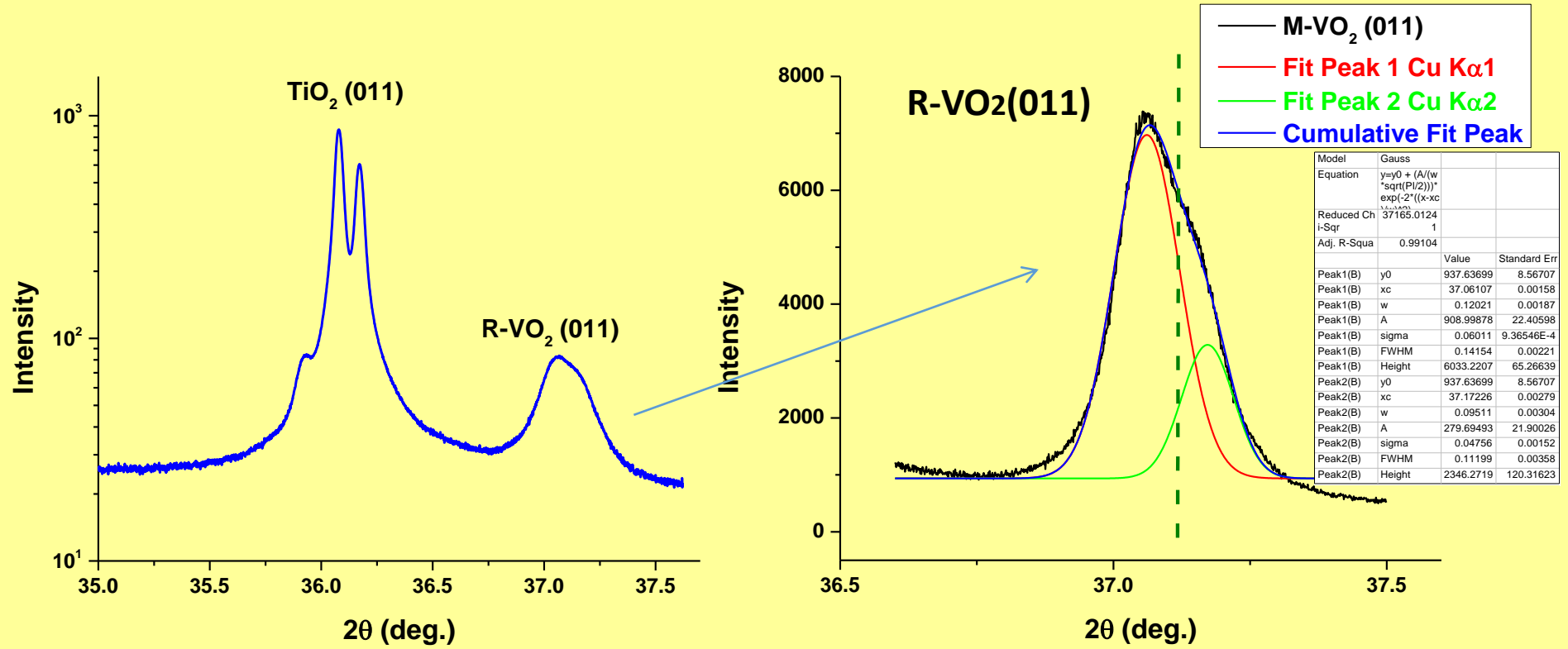
- We have explored how films on Al_2O_3 and TiO_2 have different MIT dynamics at various temperatures
- Future work: to explain the differences in MIT dynamic thresholds between different films.

Properties of Our Thin Films

<i>VO₂ on Al₂O₃</i>	<i>VO₂ on SiO₂</i>	<i>VO₂ on TiO₂</i>
Crystalline M-VO ₂ (020) with in plane 6-fold symmetry	Out of plane M-VO ₂ (011), in plane polycrystalline	R-VO ₂ (011) monocrystalline
Average Grain size out of plane=447 Å In plane=93Å	Average Grain size=367Å	Average Grain size out of plane=593Å In plane=179Å
T _c = 341K	T _c =324K	T _c =306K
Strain In plane: -0.53% Out of plane: -2.81%	Strain Out of plane: 0.92%	Strain In plane: 0.14% Out of plane: 0.54%

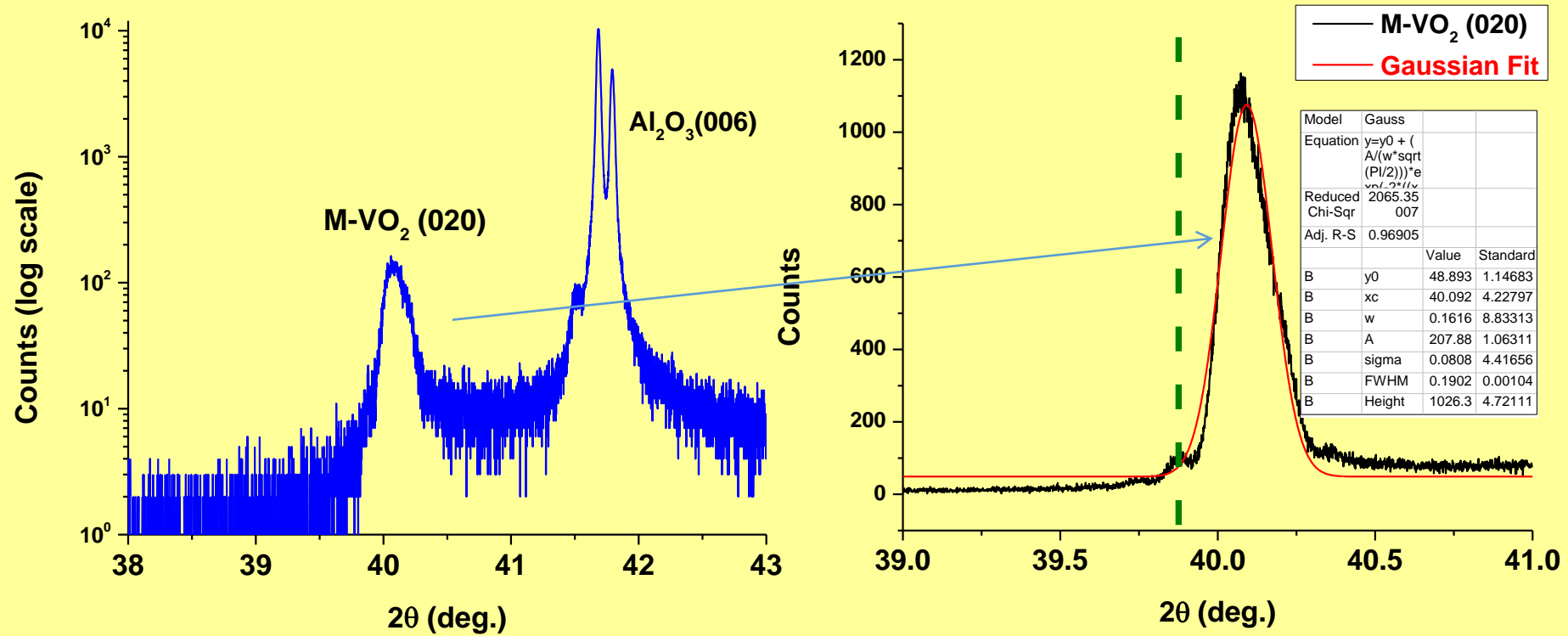
L121611B1 VO₂_TiO₂ (011)

Symmetric scan



L080611A1 VO₂_c-Al₂O₃

Symmetric scan



We can probe this phase transition by looking at the reflected and transmitted light.

